

Appl. No. 10/761,702  
Examiner: Warren, Matthew E, Art Unit 2815  
In response to the Office Action dated March 10, 2005

Date: July 11, 2005  
Attorney Docket No. 10113671

#### AMENDMENTS TO THE SPECIFICATION

Please replace the paragraph at page 5, line 4 with the following amended paragraph:

-In order to achieve the described objects, the present invention provides a bit line contact structure comprising a substrate and dielectric layer. The substrate has a transistor thereon, further comprising a raised gate electrode, a drain region, and a source region. The dielectric layer, of spin-coating material, is formed ~~blanketly~~ directly on the transistor. The dielectric layer further has an opening exposing the drain region.